

SANYO	No.2392A	2SK772
		N-Channel Junction Silicon FET
		AF Amp Applications

Applications

Variable resistors, analog switches, AF amp, constant-current circuit

Features

Adoption of FBET process

Absolute Maximum Ratings at Ta=25°C

			unit
Drain to Source Voltage	V_{DSX}	40	V
Gate to Source Voltage	V_{GDS}	-40	V
Gate Current	I_G	10	mA
Drain Current	I_D	20	mA
Allowable Power Dissipation	P_D	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

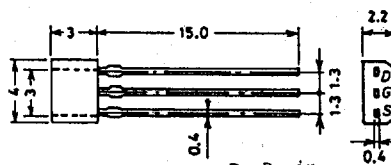
			min	typ	max	unit
Gate to Drain Breakdown Voltage	$V_{(BR)GDS}$	$I_G = -10\mu A, V_{DS} = 0$	-40			V
Gate Cutoff Current	I_{GSS}	$V_{GS} = -20V, V_{DS} = 0$			-1.0	nA
Cutoff Voltage	$I_{GS(off)}$	$V_{DS} = 10V, I_D = 1\mu A$	-0.3	-0.9	-2.5	V
Drain Current	I_{DSS}	$V_{DS} = 10V, V_{GS} = 0$	1.2*		12.0*	mA
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, V_{GS} = 0, f = 1kHz$	4.5	9.0		mS
Input Capacitance	c_{iss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		9.0		pF
Reverse Transfer Capacitance	c_{rss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		2.1		pF
Noise Figure	NF	$V_{DS} = 10V, R_g = 1k\Omega, I_D = 1mA, f = 1kHz$		1.5		dB

*: The 2SK772 is classified by I_{DSS} as follows: (unit:mA)

1.2	D	3.0	2.5	E	6.0	5.0	F	12.0
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Case Outline 2034

(unit:mm)



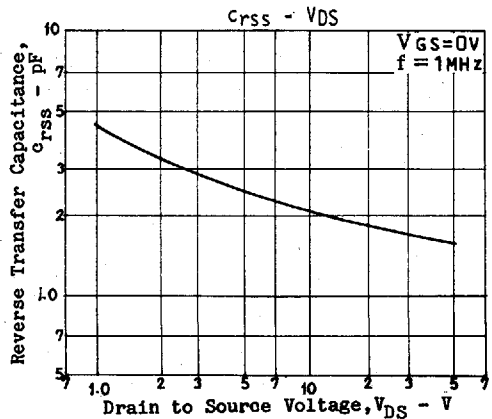
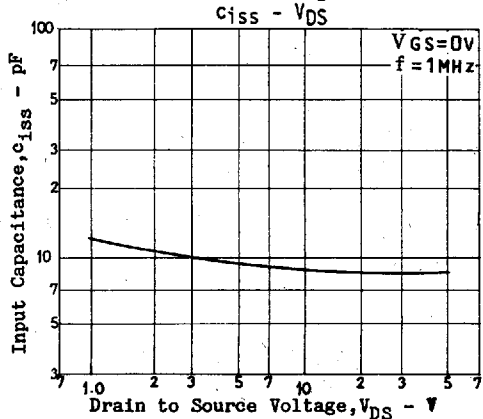
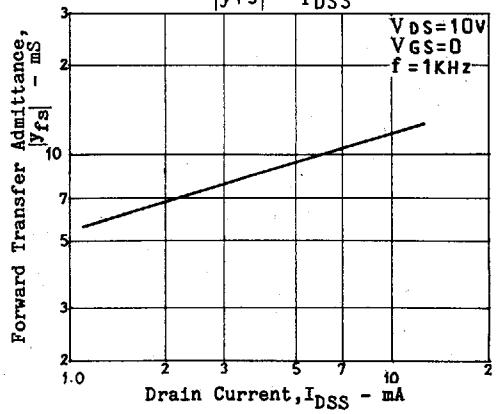
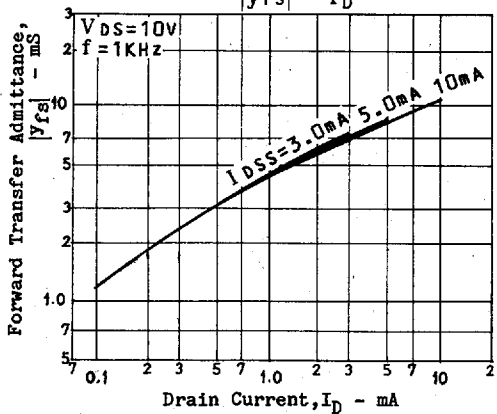
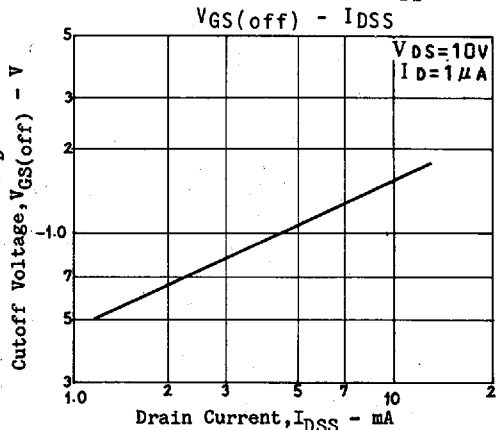
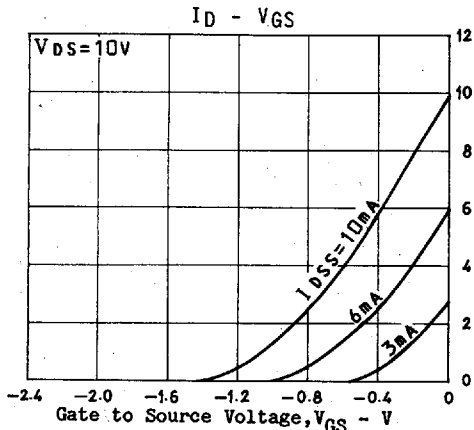
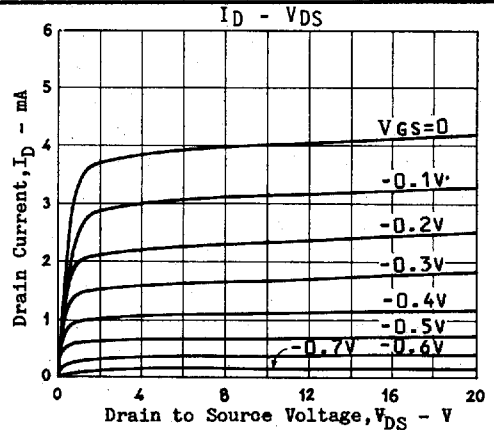
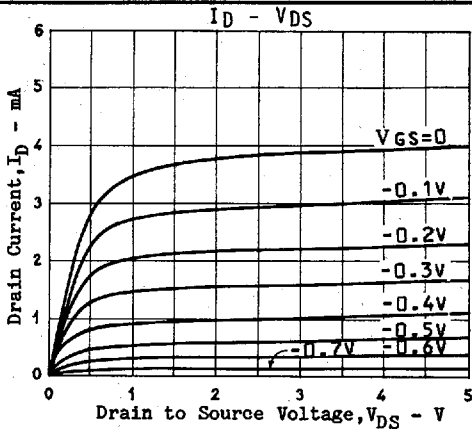
D: Drain
G: Gate
S: Source

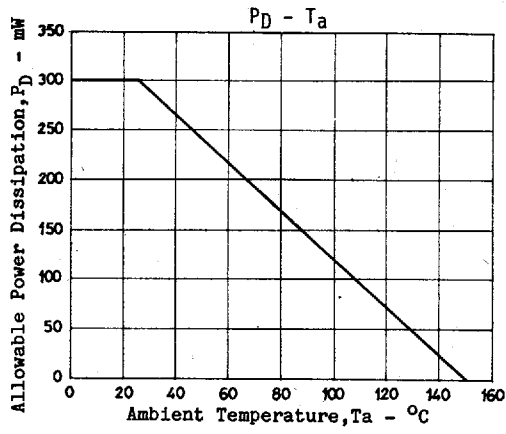
SANYO: SPA

Specifications and information herein are subject to change without notice.

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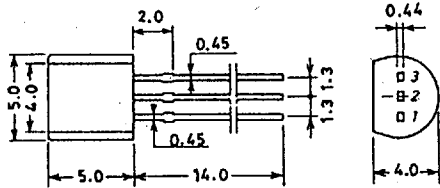




CASE OUTLINES OF LEAD FORMED SMALL SIGNAL TRANSISTORS

- All of Sanyo lead formed small signal transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

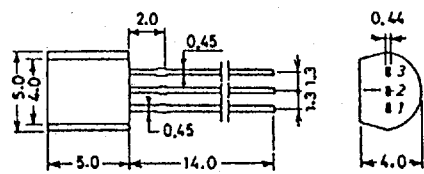
Case Outline 2003A/2003B (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Emitter
2 : Collector
3 : Base

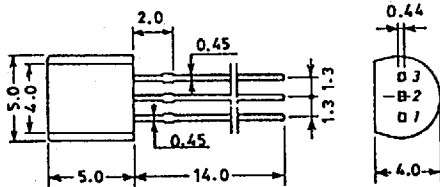
Case Outline 2019A/2019B (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Source
2 : Gate
3 : Drain

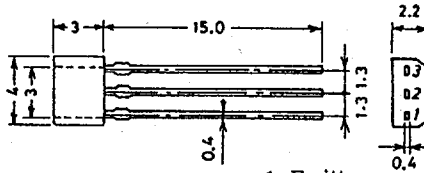
Case Outline 2004A (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Base
2 : Emitter
3 : Collector

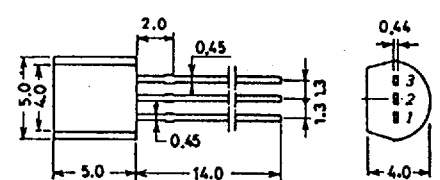
Case Outline 2033 (unit : mm)



1 : Emitter
2 : Collector
3 : Base

SANYO : SPA

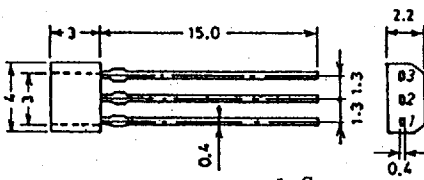
Case Outline 2005A (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Drain
2 : Source
3 : Gate

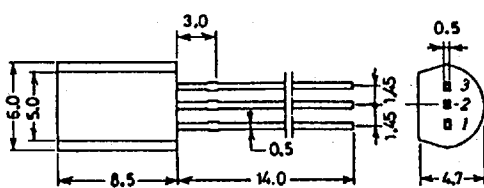
Case Outline 2034/2034A (unit : mm)



1 : Source
2 : Gate
3 : Drain

SANYO : SPA

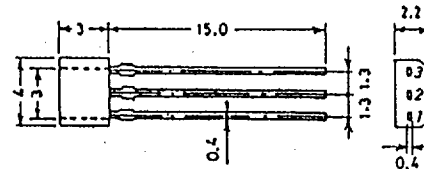
Case Outline 2006A (unit : mm)



EIAJ : SC-51
SANYO : MP

1 : Emitter
2 : Collector
3 : Base

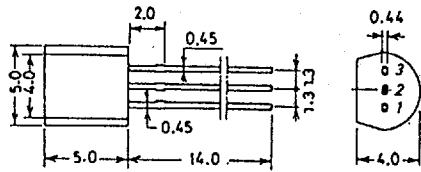
Case Outline 2040 (unit : mm)



1 : Drain
2 : Source
3 : Gate

SANYO : SPA

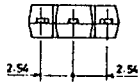
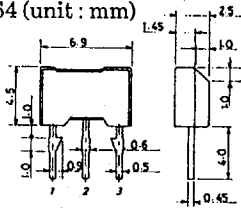
Case Outline 2061 (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1: Emitter
2: Base
3: Collector

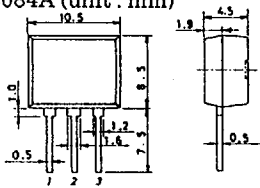
Case Outline 2064 (unit : mm)



1: Emitter
2: Collector
3: Base

SANYO : NMP

Case Outline 2084A (unit : mm)



1: Emitter
2: Collector
3: Base

SANYO : FLP